N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)[a, e]	Q_g (Typ)
30	0.0022 at V_{GS} = 10 V	90	82 nC
	0.0027 at V_{GS} = 4.5 V	90	

FEATURES

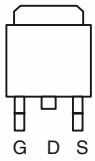
- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested

RoHS COMPLIANT

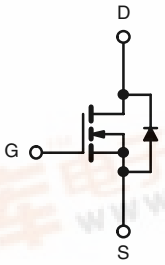
APPLICATIONS

- OR-ing
- Server

TO-263



Top View



N-Channel MOSFET

Ordering Information: SUM90N03-2m2P-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 175 °C)	T_C = 25 °C	I_D	90[a, e]	A
	T_C = 70 °C		90[e]	
	T_A = 25 °C		33[b, c]	
	T_A = 70 °C		29.8[b, c]	
Pulsed Drain Current		I_{DM}	200	
Avalanche Current Pulse	L = 0.1 mH	I_{AS}	36	
Single Pulse Avalanche Energy		E_{AS}	64.8	V
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	90[a, e]	A
	T_A = 25 °C		3.13[b, c]	
Maximum Power Dissipation	T_C = 25 °C	P_D	250[a]	W
	T_C = 70 °C		175	
	T_A = 25 °C		3.75[b, c]	
	T_A = 70 °C		2.63[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[b, d]	t ≤ 10 s	R_{thJA}	32	40	°C/W
Maximum Junction-to-Case	Steady State	R_{thJC}	0.5	0.6	

Notes:
a. Based on T_C = 25 °C.
b. Surface Mounted on 1" x 1" FR4 board.
c. t = 10 s.
d. Maximum under Steady State conditions is 90 °C/W.
e. Calculated based on maximum junction temperature. Package limitation current is 90 A.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min**	**Typ**	**Max**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		35		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 7.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1.5		2.5	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V			1	µA
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 55 °C			10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	90			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 32 A		0.0018	0.0022	Ω
		V_{GS} = 4.5 V, I_D = 29 A		0.0022	0.0027	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 32 A		160		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz		12065		pF
Output Capacitance	C_{oss}			1725		
Reverse Transfer Capacitance	C_{rss}			970		
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 10 V, I_D = 32 A		171	257	nC
		V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 29 A		81.5	123	
Gate-Source Charge	Q_{gs}			34		
Gate-Drain Charge	Q_{gd}			29		
Gate Resistance	R_g	f = 1 MHz		1.4	2.1	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 0.555 Ω $I_D \cong$ 27 A, V_{GEN} = 10 V, R_g = 1 Ω		18	27	ns
Rise Time	t_r			11	17	
Turn-Off Delay Time	$t_{d(off)}$			70	105	
Fall Time	t_f			10	15	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 0.625 Ω $I_D \cong$ 24 A, V_{GEN} = 4.5 V, R_g = 1 Ω		55	83	
Rise Time	t_r			180	270	
Turn-Off Delay Time	$t_{d(off)}$			55	83	
Fall Time	t_f			12	18	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			90	A
Pulse Diode Forward Current[a]	I_{SM}				200	
Body Diode Voltage	V_{SD}	I_S = 22 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 20 A, di/dt = 100 A/µs, T_J = 25 °C		52	78	ns
Body Diode Reverse Recovery Charge	Q_{rr}			70.2	105	nC
Reverse Recovery Fall Time	t_a			27		ns
Reverse Recovery Rise Time	t_b			25		

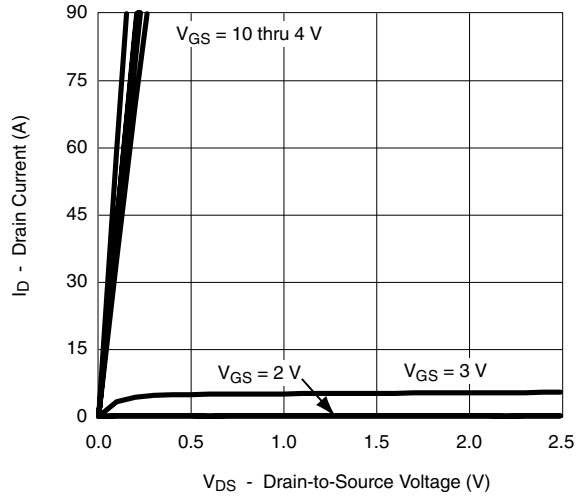
Notes:

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

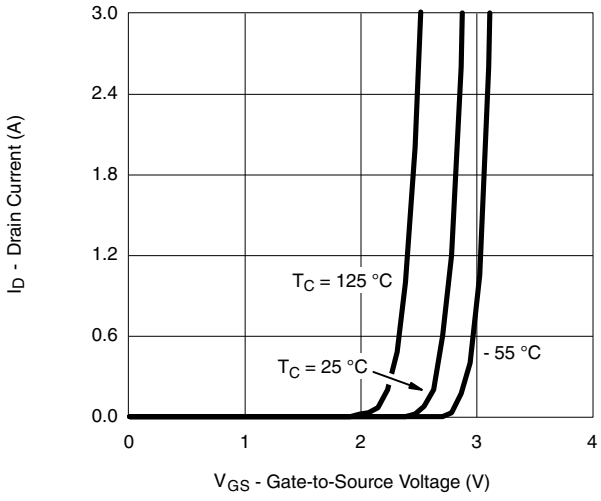
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

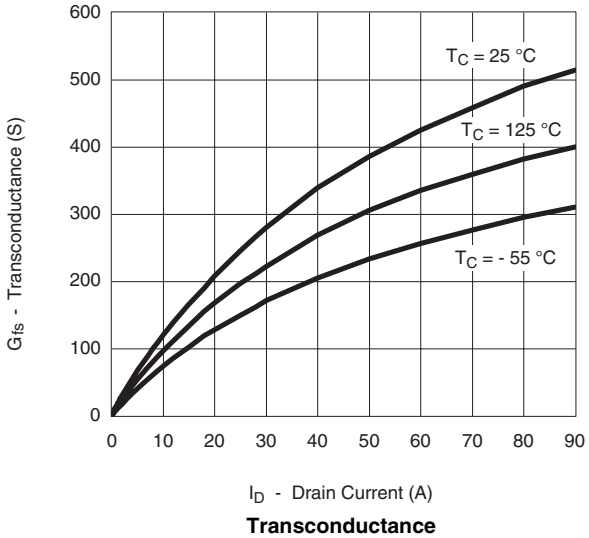
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



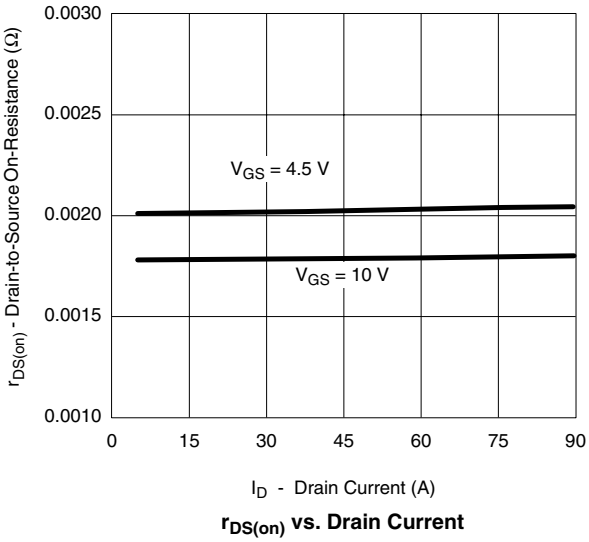
Output Characteristics



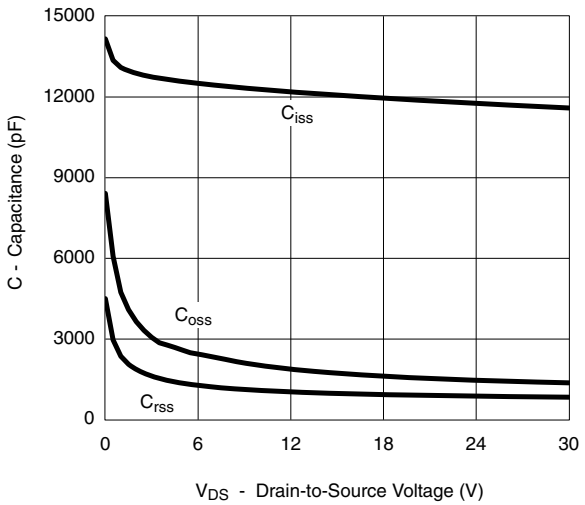
Transfer Characteristics



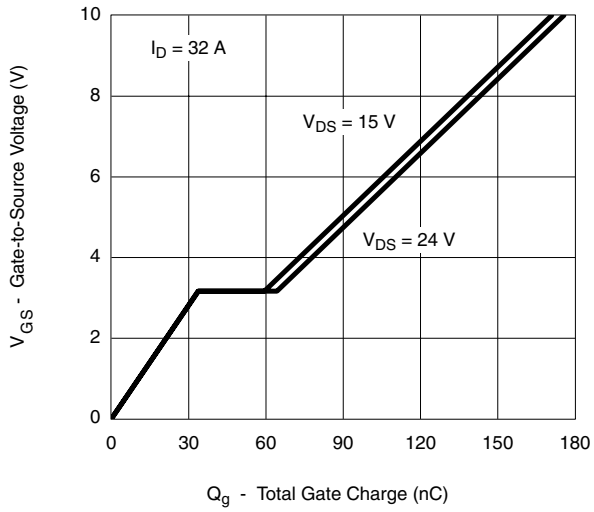
Transconductance



$r_{DS(on)}$ vs. Drain Current

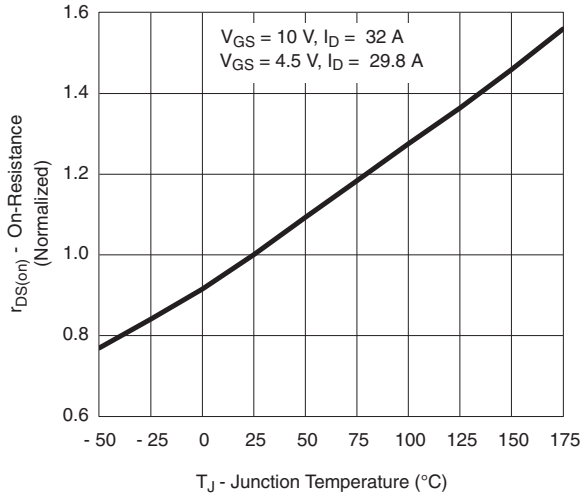


Capacitance

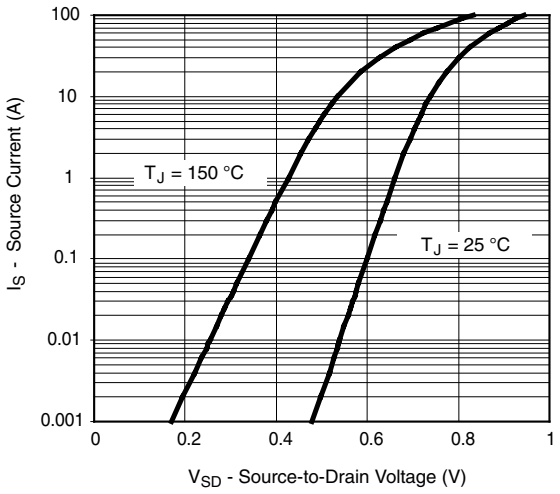


Gate Charge

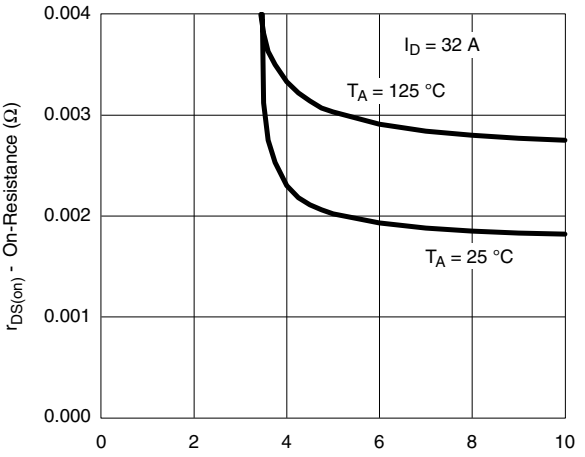
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



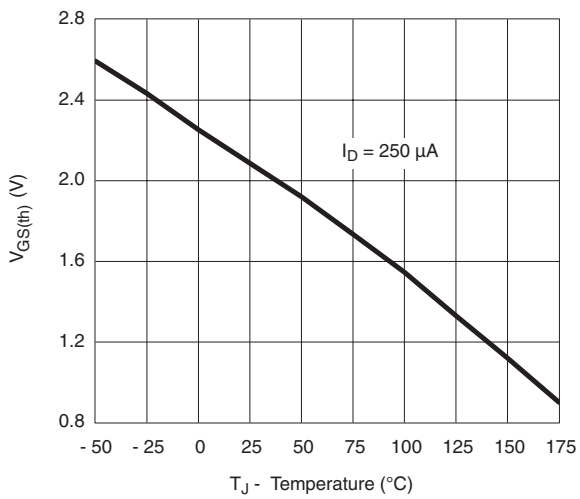
On-Resistance vs. Junction Temperature



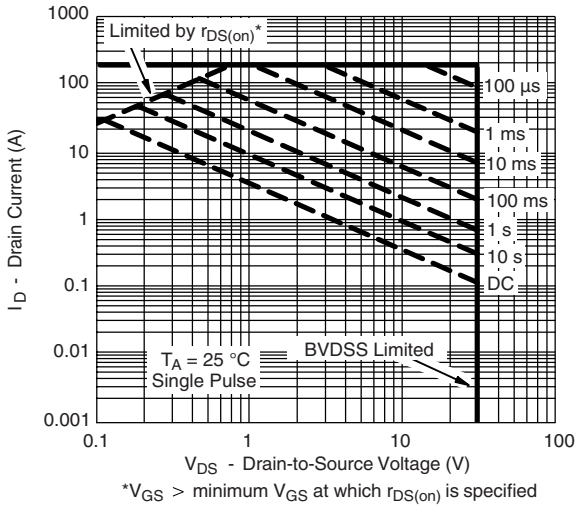
Forward Diode Voltage vs. Temperature



$r_{DS(on)}$ vs. V_{GS} vs. Temperature



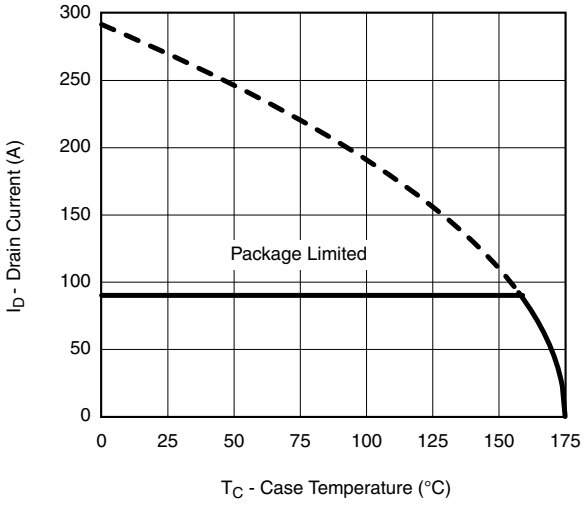
Threshold Voltage



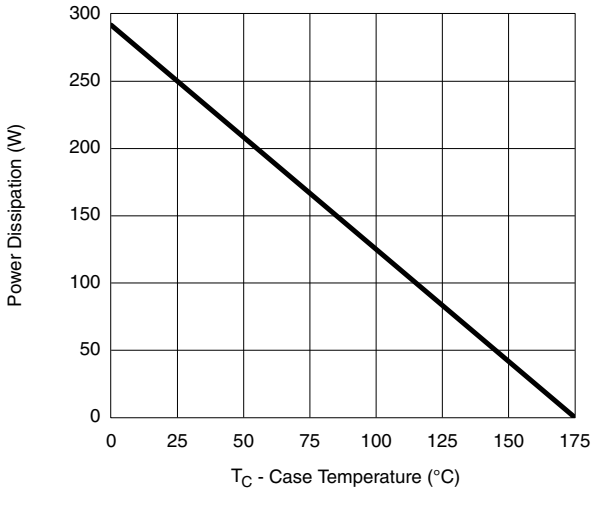
*V_{GS} > minimum V_{GS} at which $r_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

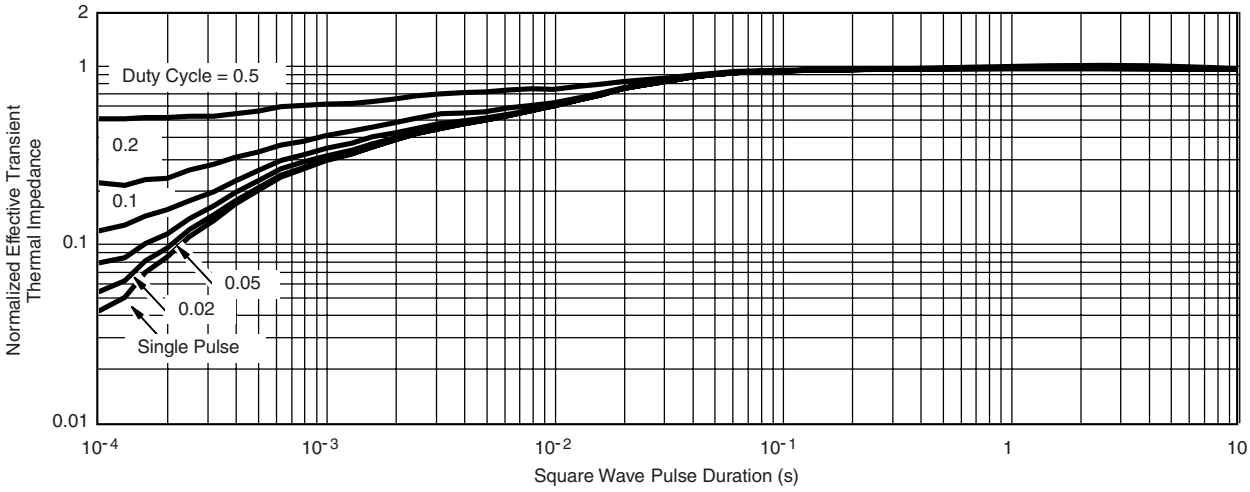


Current Derating*



Power Derating

* The power dissipation P_D is based on $T_{J(max)}$ = 175 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?74342

Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay’s terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.